

General Description

The HSU5N25 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent $R_{DS(on)}$ and gate charge for most of the synchronous buck converter applications.

The HSU5N25 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

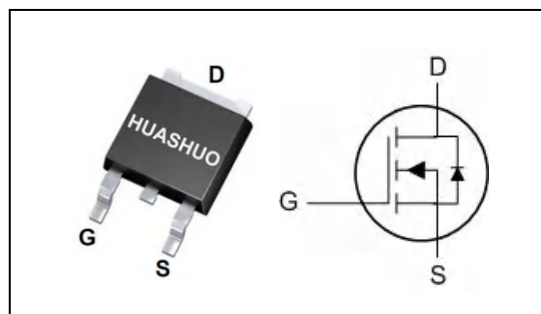
Features

- Super Low Gate Charge
- Green Device Available
- Excellent C_{dv}/dt effect decline
- Advanced high cell density Trench Technology

Product Summary

V_{DS}	250	V
$R_{DS(ON),max}$	1.2	Ω
I_D	5	A

TO252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	5	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	3	A
I_{DM}	Pulsed Drain Current ²	16	A
EAS	Single Pulse Avalanche Energy ³	16	mJ
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	2.7	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	70	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	4	$^\circ C/W$

N-Ch 250V Fast Switching MOSFETs
Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	250	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=1A$	---	970	1200	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1	1.8	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=250V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=250V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=1A$	---	7.9	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.8	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=100V, V_{GS}=10V, I_D=1A$	---	12.5	---	nC
Q_{gs}	Gate-Source Charge		---	2	---	
Q_{gd}	Gate-Drain Charge		---	2.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=100V, V_{GS}=10V, R_G=6\Omega$ $I_D=1A$	---	13	---	ns
T_r	Rise Time		---	9	---	
$T_{d(off)}$	Turn-Off Delay Time		---	38	---	
T_f	Fall Time		---	8	---	
C_{iss}	Input Capacitance	$V_{DS}=100V, V_{GS}=0V, f=1\text{MHz}$	---	670	---	pF
C_{oss}	Output Capacitance		---	14	---	
C_{rss}	Reverse Transfer Capacitance		---	8	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	5	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	16	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=1A, di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	75	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	270	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$

3.The power dissipation is limited by 150°C junction temperature

4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

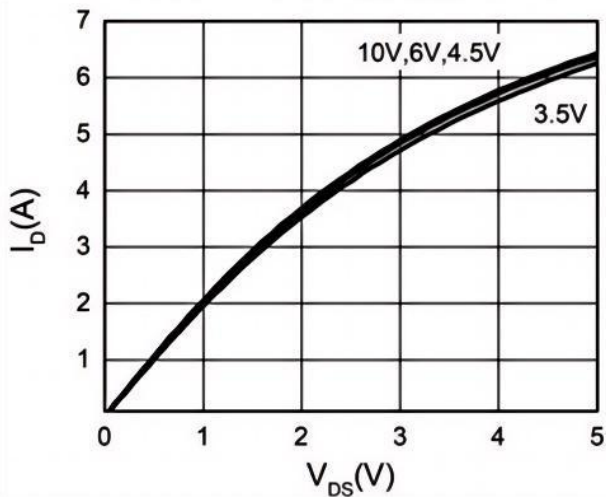


Fig.1 Typical Output Characteristics

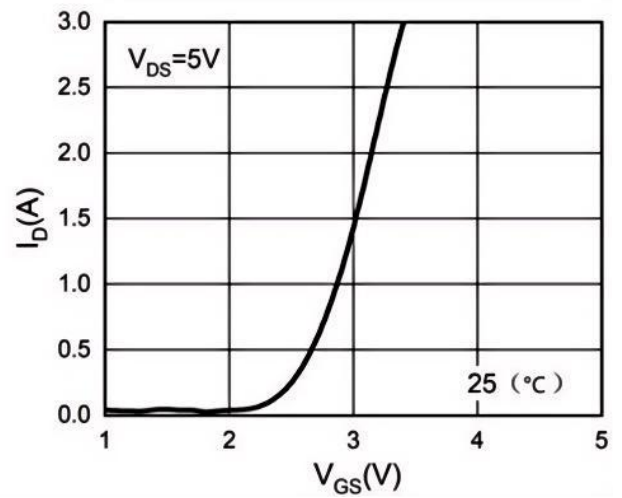


Fig.2 Transfer Characteristics

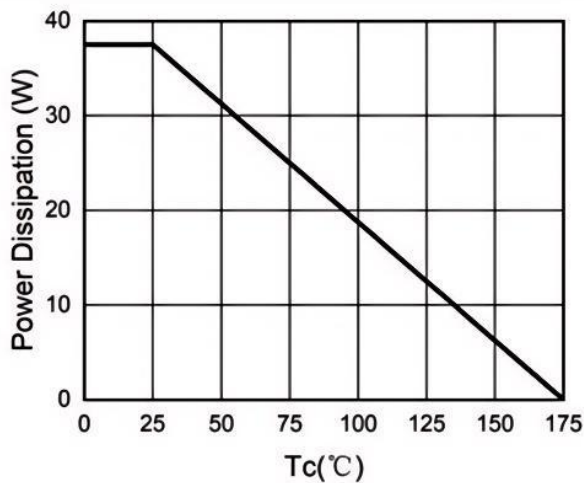


Fig.3 Power Dissipation

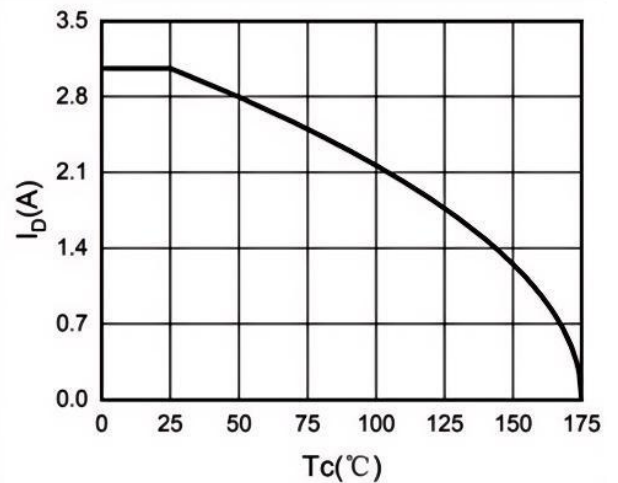


Fig.4 Drain Current

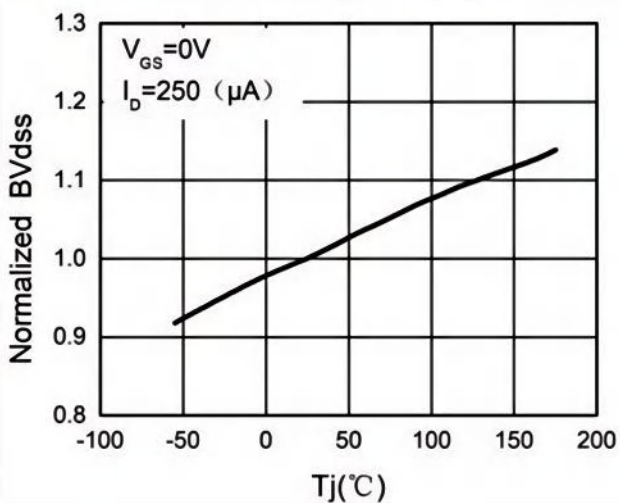


Fig.5 BV_{DS} vs Junction Temperature

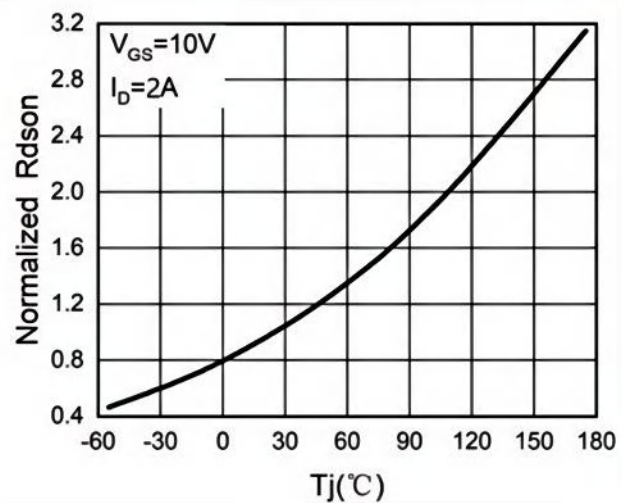


Fig.6 $R_{DS(ON)}$ vs Junction Temperature

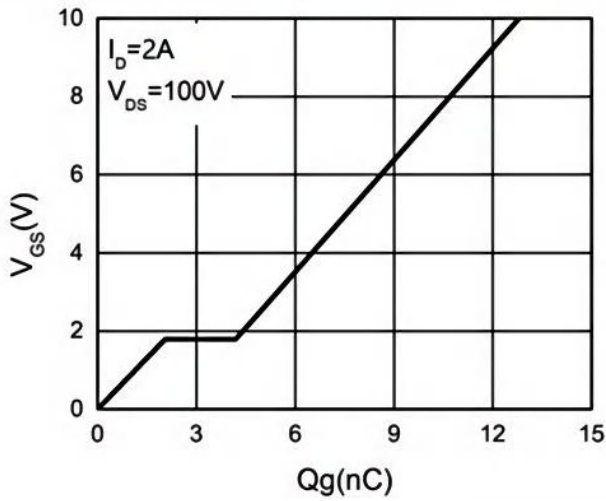


Fig.7 Gate Charge Waveforms

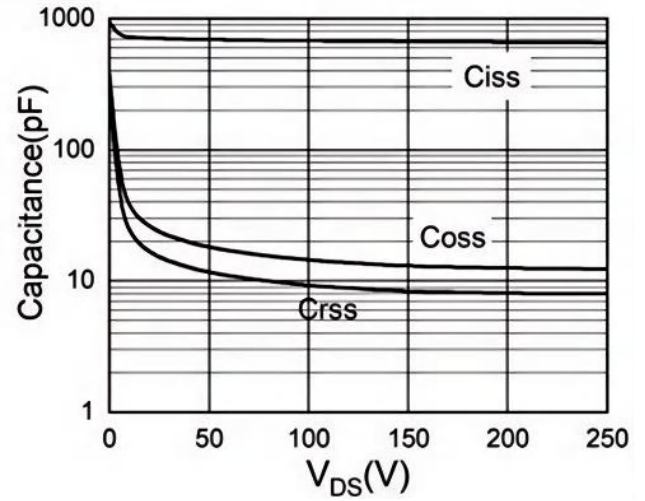


Fig.8 Capacitance

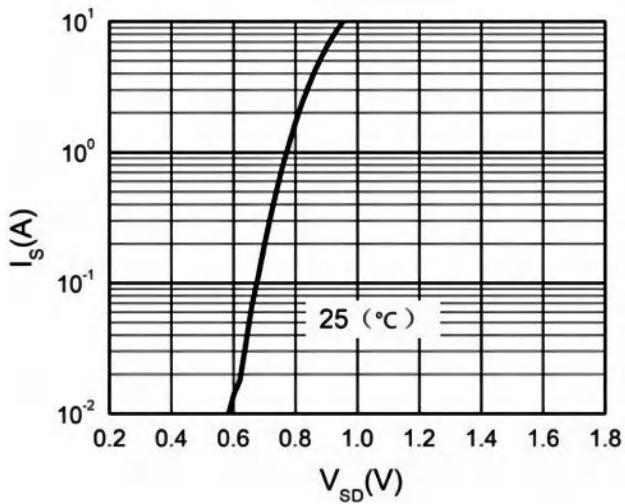


Fig.9 Body Diode Characteristics

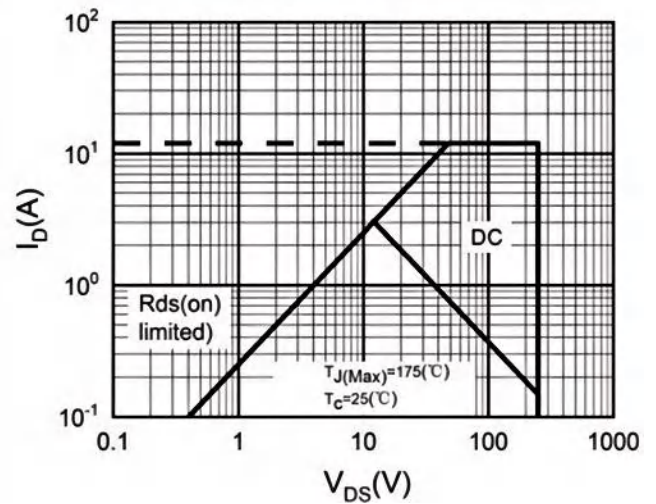
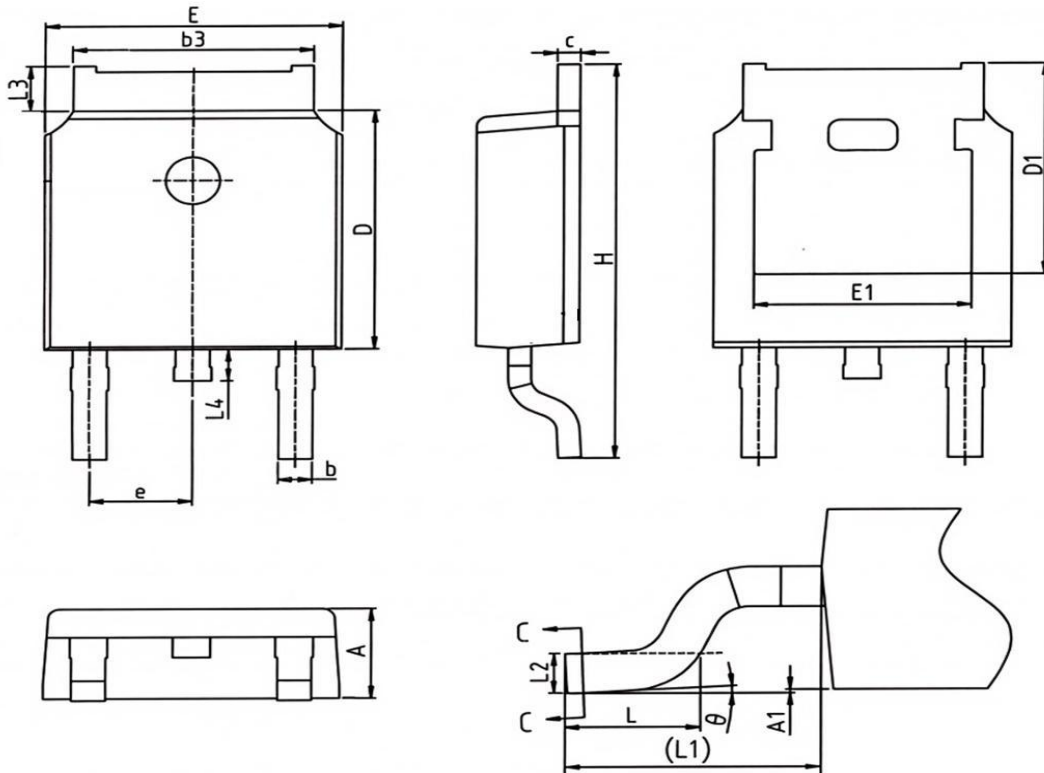


Fig.10 Maximum Safe Operating Area

Ordering Information

Part Number	Package code	Packaging
HSU5N25	TO252	2500/Tape&Reel

TO252 Package Outline



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.18	2.40	0.086	0.095
A1	-	0.2	-	0.008
b	0.68	0.9	0.026	0.036
b3	4.95	5.46	0.194	0.215
C	0.43	0.89	0.017	0.035
D	5.97	6.22	0.235	0.245
D1	5.300REF		0.209REF	
E	6.35	6.73	0.250	0.265
E1	4.32	---	0.170	-
e	2.286BSC		0.09BSC	
H	9.4	10.5	0.370	0.413
L	1.38	1.78	0.054	0.070
L1	2.90REF		0.114REF	
L2	0.51BSC		0.020BSC	
L3	0.88	1.28	0.034	0.050
L4	0.5	1	0.019	0.039
θ	0°	8°	0°	8°

HSU5N25 Marking:

